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(54) METHOD OF CLEANING SEMICONDUCTOR SUBSTRATE

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a cleaning method for suppressing corrosion of a metal film, in the cleaning of a semiconductor substrate which has a metallic film.

SOLUTION: The surface of a semiconductor substrate which has a metal film is cleaned, while preventing the corrosion of the metal film, using cleaning liquid consisting of (1) hydrogen peroxide water, ozone water, or electrolytic anode water, (2) inorganic acid or an alkaline agent, and (3) a complexing agent and/or an interface activator.

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